



Micro Commercial Components
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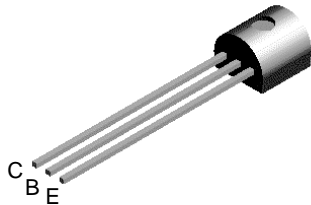
S9015

PNP Silicon Transistors

Features

- TO-92 Plastic-Encapsulate Transistors
- Capable of 0.45Watts($T_{amb}=25^{\circ}C$) of Power Dissipation.
- Collector-current 0.1A
- Collector-base Voltage 50V
- Operating and storage junction temperature range: $-55^{\circ}C$ to $+150^{\circ}C$
- Marking Code: S9015

Pin Configuration



Electrical Characteristics @ $25^{\circ}C$ Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu A_{dc}$, $I_E=0$)	50	---	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=1.0mA_{dc}$, $I_E=0$)	45	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E=100\mu A_{dc}$, $I_C=0$)	5.0	---	Vdc
I_{CBO}	Collector Cutoff Current ($V_{CB}=50V_{dc}$, $I_E=0$)	---	0.05	μA_{dc}
I_{EBO}	Emitter Cutoff Current ($V_{EB}=5.0V_{dc}$, $I_C=0$)	---	0.05	μA_{dc}

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C=1.0mA_{dc}$, $V_{CE}=5.0V_{dc}$)	60	1000	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=100mA_{dc}$, $I_E=10mA_{dc}$)	---	0.3	Vdc
$V_{BE(sat)}$	Base-Emitter Saturation Voltage ($I_C=100mA_{dc}$, $I_E=10mA_{dc}$)	---	1.0	Vdc

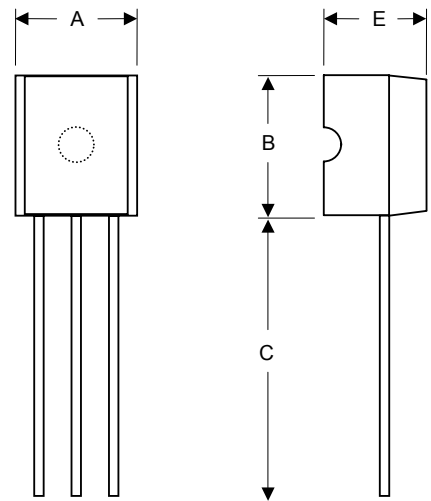
SMALL-SIGNAL CHARACTERISTICS

f_T	Transistor Frequency ($I_C=10mA_{dc}$, $V_{CE}=5.0V_{dc}$, $f=30MHz$)	150	---	MHz
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CLASSIFICATION OF $h_{FE(1)}$

Rank	A	B	C1	C2	C3	D
Range	60-150	120-200	200-300	300-400	400-500	500-1000

TO-92



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	